

Vertical power MOSFET having thick metal layer to reduce distributed resistance and method of fabricating the same

Patent Number: EP0720234

Publication date: 1996-07-03

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Requested Patent: EP0720234, A3

Application Number: EP19950309537 19951229

Priority Number(s): US19940367486 19941230

IPC Classification: H01L29/417; H01L29/78; H01L29/739; H01L23/482

EC Classification: H01L23/485A, H01L23/482E, H01L29/417D4

Equivalents: JP8255911, US5665996

Cited Documents: US5349239; FR1397424; JP60225467; JP62132345; JP6120292

Abstract

The on-resistance of a vertical power transistor is substantially reduced by forming a thick metal layer on top of the relatively thin metal layer that is conventionally used to make contact with the individual transistor cells in the device. The thick metal layer is preferably plated electrolessly on the thin metal layer through an

opening that is formed in the passivation layer. 

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